

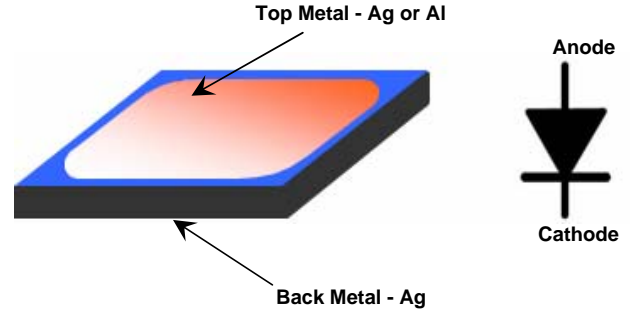
Schottky Rectifier Die Specification

40V 1A,32mil Schottky Rectifier, Standard VF

Product Type:GDSB140-32

Main Products Characteristics

- Average forward current: $I_{F(AV)} = 1\text{ A}$
- Maximum operating junction temperature: $T_j = 125\text{ }^\circ\text{C}$
- Top metal: Ag or Al
- Wafer size: 6"
- PDPW: 23,500die/Wafer



Maximum Ratings

Parameter	Symbol	Rating
		GD SB140-32
Repetitive peak reverse voltage	V_{RRM}	40 V
Average forward current	$I_{F(AV)}$	1 A
Non-repetitive peak surge current ($t_p = 8.3\text{ ms}$, halfwave, 1 cycle)	I_{FSM}	30 A
Storage temperature range	T_{stg}	-50 to +125 $^\circ\text{C}$
Maximum operating junction temperature	T_j	125 $^\circ\text{C}$

Static Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value
		GD SB140-32
Reverse breakdown voltage $I_R = 1\text{ mA}$	V_{BR}	45 V (Typical 52V)
Maximum forward voltage drop $I_F = 1\text{ A}$ Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$	V_F	0.50 V (Typical 0.47V)
Maximum reverse current $V_R = V_{RRM}$ Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$	I_R	0.1mA (Typical 0.015mA)

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	32 Mils
Top Metal Pad	28 Mils
Active Area	25 Mils
Top Metal	Ag or Al
Back Metal	Ag

Note: 1 *: Also can offer device with other thickness (8~15 mils)
2 **: Cutting street width is around 0.7 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Suzhou Goodark does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.